

# T810H

# High temperature 8 A sensitive TRIACs

## Features

- Medium current TRIAC
- Logic level sensitive TRIAC
- 150 °C max. T<sub>i</sub> turn-off commutation
- Clip bounding
- RoHS (2002/95/EC) compliant packages

## **Applications**

- The T810H is designed for the control of AC actuators in appliances and industrial systems.
- The multi-port drive of the microcontroller can control the multiple loads of such appliances and systems through these sensitive gate TRIACs.

## Description

Specifically designed to operate at 150 °C, the new 8 A T810H TRIACs provide an enhanced performance in terms of power loss and thermal dissipation. This allows the optimization of the heatsink size, leading to space and cost effectiveness when compared to electromechanical solutions.

Based on ST logic level technology, they offer an  $I_{GT}$  lower than 10 mA and specified minimal commutation and high noise immunity levels valid up to the  $T_i$  max.

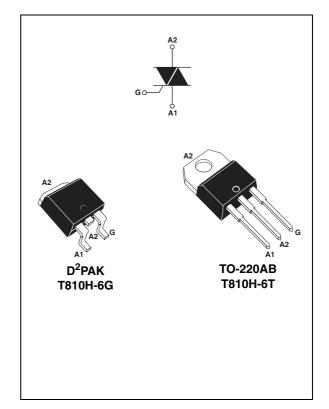


Table 1.	Device	summary
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Symbol	Value	Unit
I <sub>T(RMS)</sub>	8	А
V <sub>DRM</sub> /V <sub>RRM</sub>	600	V
I <sub>GT MAX</sub>	10	mA

# 1 Characteristics

Symbol	Param	Value	Unit		
I <sub>T(RMS)</sub>	On-state rms current (full sine wave)	D <sup>2</sup> PAK, TO-220AB	T <sub>c</sub> = 135 °C	8	А
1	Non repetitive surge peak on-state	F = 60 Hz	t = 16.7 ms	84	•
$I_{TSM}$ current (full cycle, $T_j$ initial = 25 °C)	current (full cycle, T <sub>j</sub> initial = 25 °C)	F = 50 Hz	t = 20 ms 80		A
l <sup>2</sup> t	I <sup>2</sup> t Value for fusing	t <sub>p</sub> = 10 ms		42	A <sup>2</sup> s
dl/dt	Critical rate of rise of on-state current $I_G = 2 \ x \ I_{GT}$ , $t_r \leq 100 \ ns$	F = 120 Hz	T <sub>j</sub> = 150 °C	50	A/µs
V <sub>DSM</sub> /V <sub>RSM</sub>	Non repetitive surge peak off-state voltage	t <sub>p</sub> = 10 ms	T <sub>j</sub> = 25 °C	V <sub>DRM</sub> /V <sub>RRM</sub> + 100	V
I <sub>GM</sub>	Peak gate current $t_p = 20 \ \mu s$ $T_j = 150 \ ^{\circ}C$		4	А	
P <sub>G(AV)</sub>	Average gate power dissipation $T_j = 150 \text{ °C}$			1	W
T <sub>stg</sub> T <sub>j</sub>	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 150	°C

## Table 2. Absolute maximum ratings

### Table 3.Electrical characteristics (T<sub>i</sub> = 25 °C, unless otherwise specified)

Symbol	Test conditions	Quadrant	Min	Max.	Unit	
I <sub>GT</sub>	V 10V B 220	-    -	1	10	mA	
V <sub>GT</sub>	$V_D = 12 V R_L = 33 \Omega$	-    -		1.0	V	
V <sub>GD</sub>	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega$	1 - 11 - 111	0.15		V	
Ι <sub>Η</sub> <sup>(1)</sup>	I <sub>T</sub> = 100 mA			25	mA	
	1 101	1 - 111		30	mA	
۱L	$I_{G} = 1.2 I_{GT}$	II		35		
dV/dt <sup>(1)</sup>	$V_D = 67\% V_{DRM}$ , gate open, $T_j = 150 \text{ °C}$				V/µs	
(dl/dt)c <sup>(1)</sup>	Logic level, 0.1 V/µs, T <sub>j</sub> = 150 °C		11.4		A/mo	
(ui/ut)C ( /	Logic level, 15 V/ $\mu$ s, T <sub>j</sub> = 150 °C				A/ms	

1. For both polarities of A2 referenced to A1.



Table 4.	Static characteristics				
Symbol	Test conditions			Value	Unit
V <sub>T</sub> <sup>(1)</sup>	I <sub>TM</sub> = 11.3 A, t <sub>p</sub> = 380 μs	T <sub>j</sub> = 25 °C	MAX.	1.5	V
V <sub>t0</sub> <sup>(1)</sup>	Threshold voltage	T <sub>j</sub> = 150 °C	MAX.	0.80	V
R <sub>d</sub> <sup>(1)</sup>	Dynamic resistance	T <sub>j</sub> = 150 °C	MAX.	55.0	mΩ
I <sub>DRM</sub>		T <sub>j</sub> = 25 °C	MAX.	5	μA
	$V_{DRM} = V_{RRM}$	$T_j = 150 \ ^\circ C$	MAX.	3.1	
	$V_D/V_R = 400 V$ (at peak mains voltage)	T <sub>j</sub> = 150 °C	MAX.	2.5	mA
	$V_D/V_R = 200 V$ (at peak mains voltage)	T <sub>j</sub> = 150 °C	MAX.	2.0	

#### **F**. I. I. A

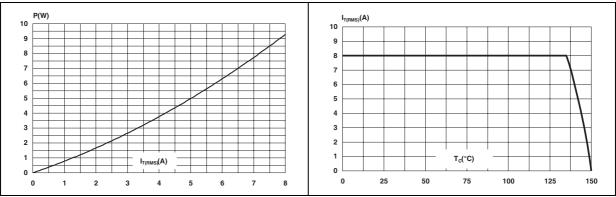
1. for both polarities of A2 referenced to A1.

#### Table 5. **Thermal resistance**

Symbol		Parameter			Unit
R <sub>th(j-c)</sub>	Junction to case (AC)		D <sup>2</sup> PAK / TO-220AB	1.60	
D	Junction to ambient	$S = 1 \text{ cm}^2$	D <sup>2</sup> PAK	45	°C/W
R <sub>th(j-a)</sub> Junction t	Junction to ambient		TO-220AB	60	

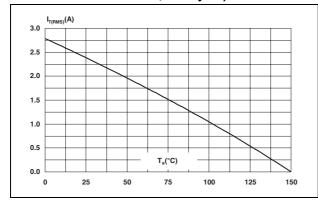
#### Maximum power dissipation versus Figure 2. Figure 1. on-state rms current (full cycle)

### On-state rms current versus case temperature (full cycle)





#### Figure 3. On-state rms current versus ambient temperature (free air convection, full cycle)



#### Figure 5. Relative variation of gate trigger Figure 6. current and voltage versus junction temperature (typical values)

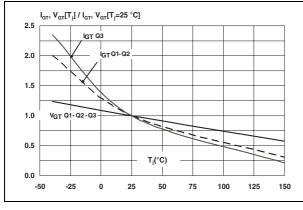
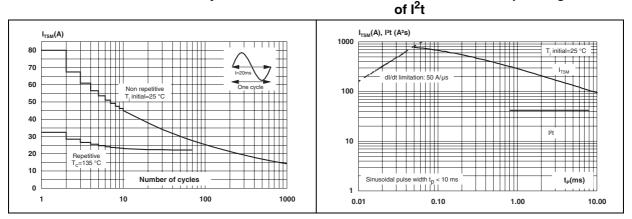
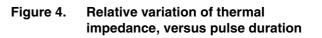


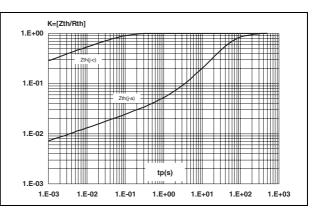
Figure 7. Surge peak on-state current versus number of cycles

Figure 8.

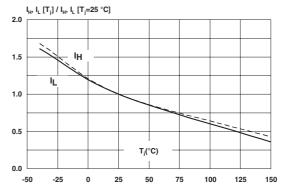
Non-repetitive surge peak on-state current and corresponding value







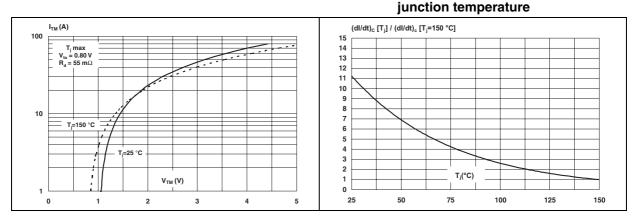
Relative variation of holding and latching current versus junction temperature (typical values)





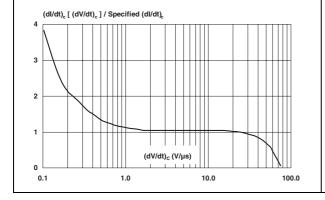


#### Figure 9. On-state characteristics (maximum Figure 10. Relative variation of critical rate of decrease of main current versus values)



#### Relative variation of critical rate of Figure 12. Figure 11. decrease of main current versus reapplied dV/dt (typical values)

Relative variation of static dV/dt immunity versus junction temperature



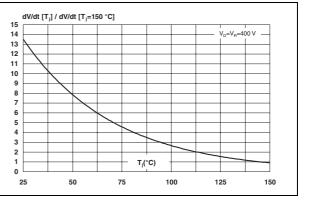
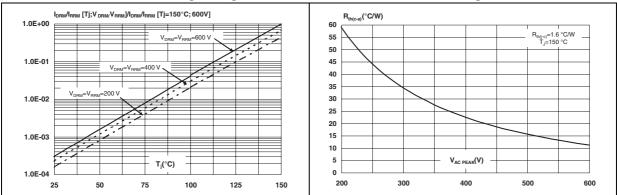
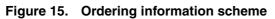


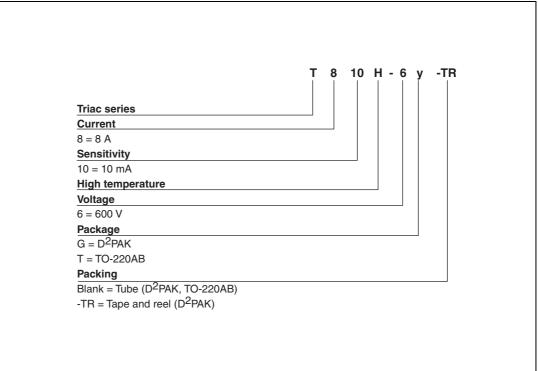
Figure 13. Variation of leakage current versus Figure 14. Acceptable case to ambient thermal junction temperature for different values of blocking voltage

resistance versus repetitive peak off-state voltage



# 2 Ordering information scheme





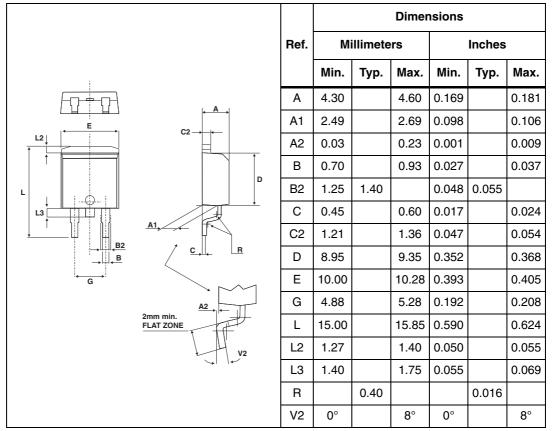
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## 3 Package information

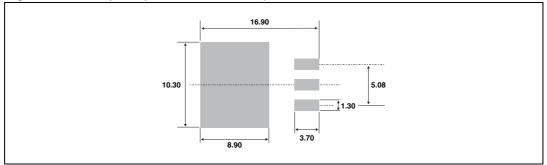
- Epoxy meets UL94, V0
- Recommended torque 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <u>www.st.com</u>. ECOPACK<sup>®</sup> is an ST trademark.

Table 6.D<sup>2</sup>PAK dimensions



### Figure 16. Footprint (dimensions in mm)





				Dimer	nsions		
	Ref.	M	illimete	rs		Inches	
		Min.	Тур.	Max.	Min.	Тур.	Max.
	А	15.20		15.90	0.598		0.625
	a1		3.75			0.147	
B C	a2	13.00		14.00	0.511		0.551
	В	10.00		10.40	0.393		0.409
	b1	0.61		0.88	0.024		0.034
	b2	1.23		1.32	0.048		0.051
I4 I3 -∰-	С	4.40		4.60	0.173		0.181
	c1	0.49		0.70	0.019		0.027
	c2	2.40		2.72	0.094		0.107
	е	2.40		2.70	0.094		0.106
	F	6.20		6.60	0.244		0.259
eel →iit	ØI	3.75		3.85	0.147		0.151
	14	15.80	16.40	16.80	0.622	0.646	0.661
	L	2.65		2.95	0.104		0.116
	12	1.14		1.70	0.044		0.066
	13	1.14		1.70	0.044		0.066
	М		2.60			0.102	

Table 7. TO-220AB dimensions



# 4 Ordering information

## Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T810H-6G	T810H 6G	D <sup>2</sup> PAK	1.5 g	50	Tube
T810H-6G-TR	T810H 6G	D <sup>2</sup> PAK	1.5 g	1000	Tape and reel
T810H-6T	T810H 6T	TO-220AB	2.3 g	50	Tube

# 5 Revision history

## Table 9.Document revision history

Date	Revision	Changes
15-May-2009	1	First issue.



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